

Supplementary Materials: Optimization of the Active Layer P3HT:PCBM for Organic Solar Cell

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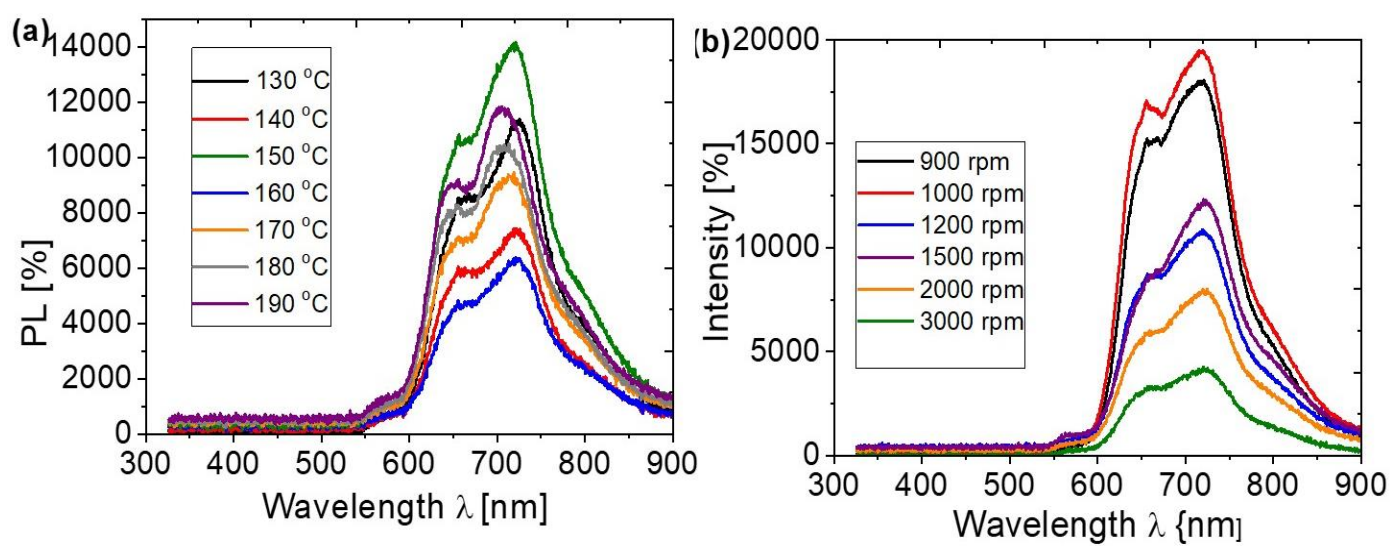


Figure S1. the photoluminescence of the P3HT:PCBM under (a) different annealing temperature, (b) different spin speed coating.

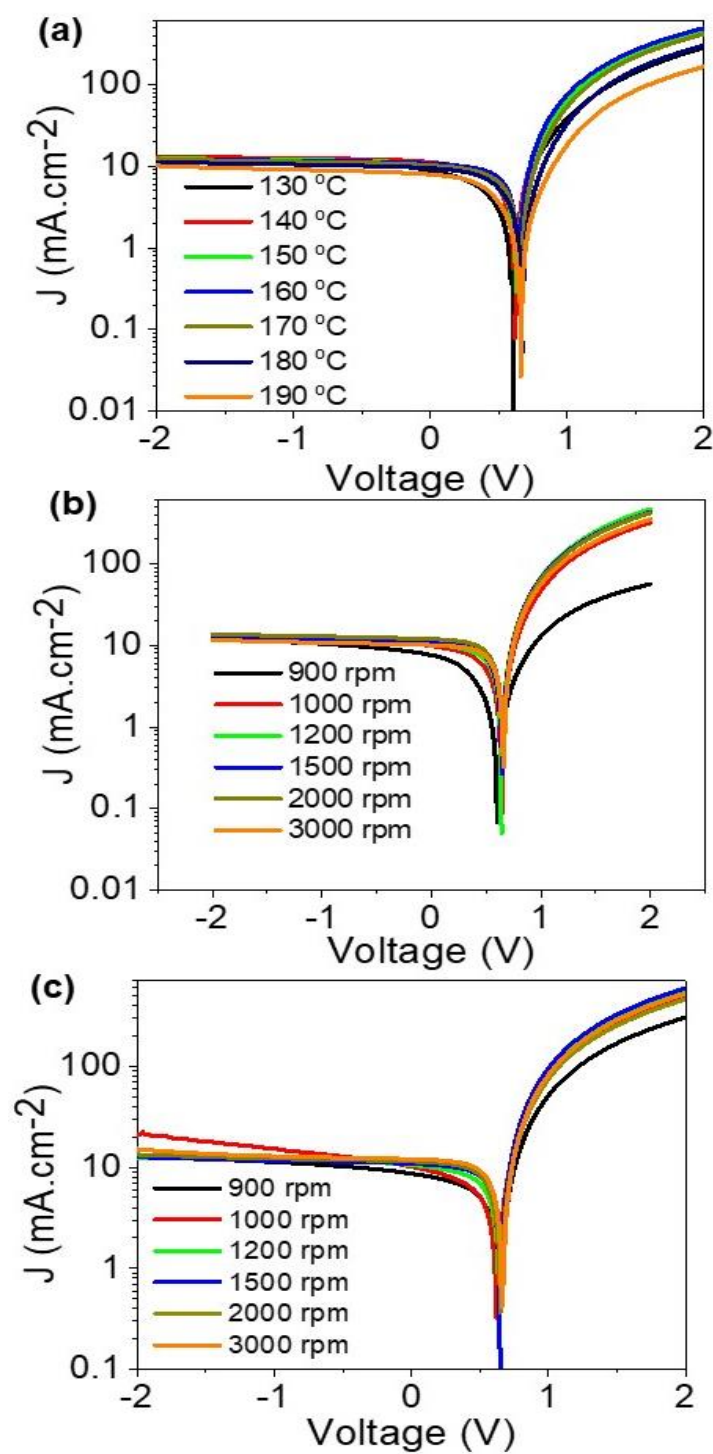


Figure S2. The integral values of I-V values in light for the effect of (a) annealing temperature, (b) spin speed coating using Al electrode, (c) spin speed coating using Mg-Al electrode.

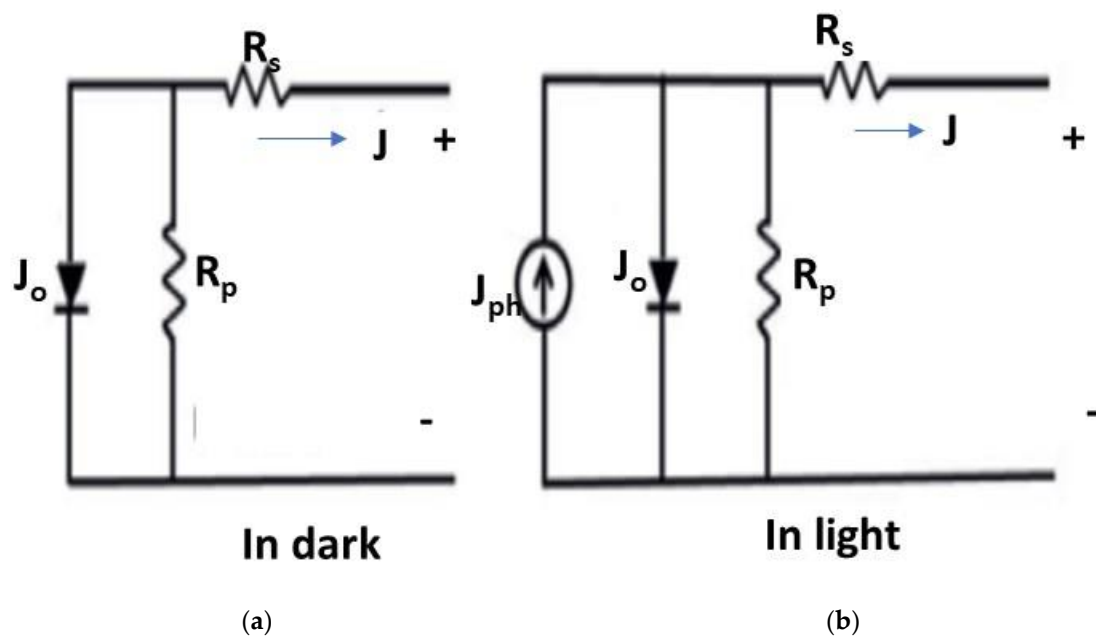


Figure S3. The equivalent circuit model represents R_s and R_p in (a) dark and (b) light.

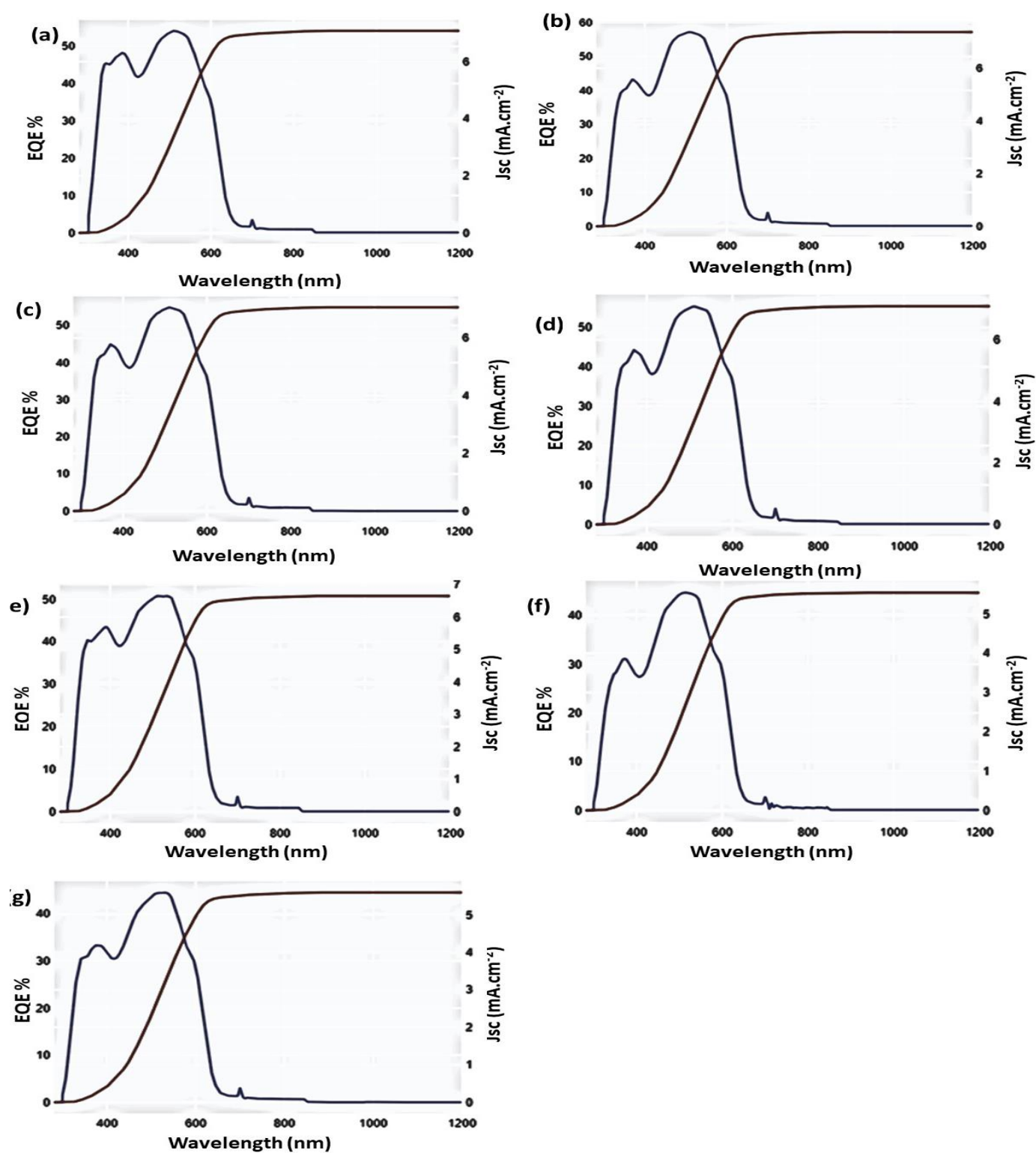


Figure S4. The J_{sc} and EQE relations under different wavelengths for (a) 130, (b) 140, (c) 150, (d) 160, (e) 170, (f) 180, and (g) 190 °C.

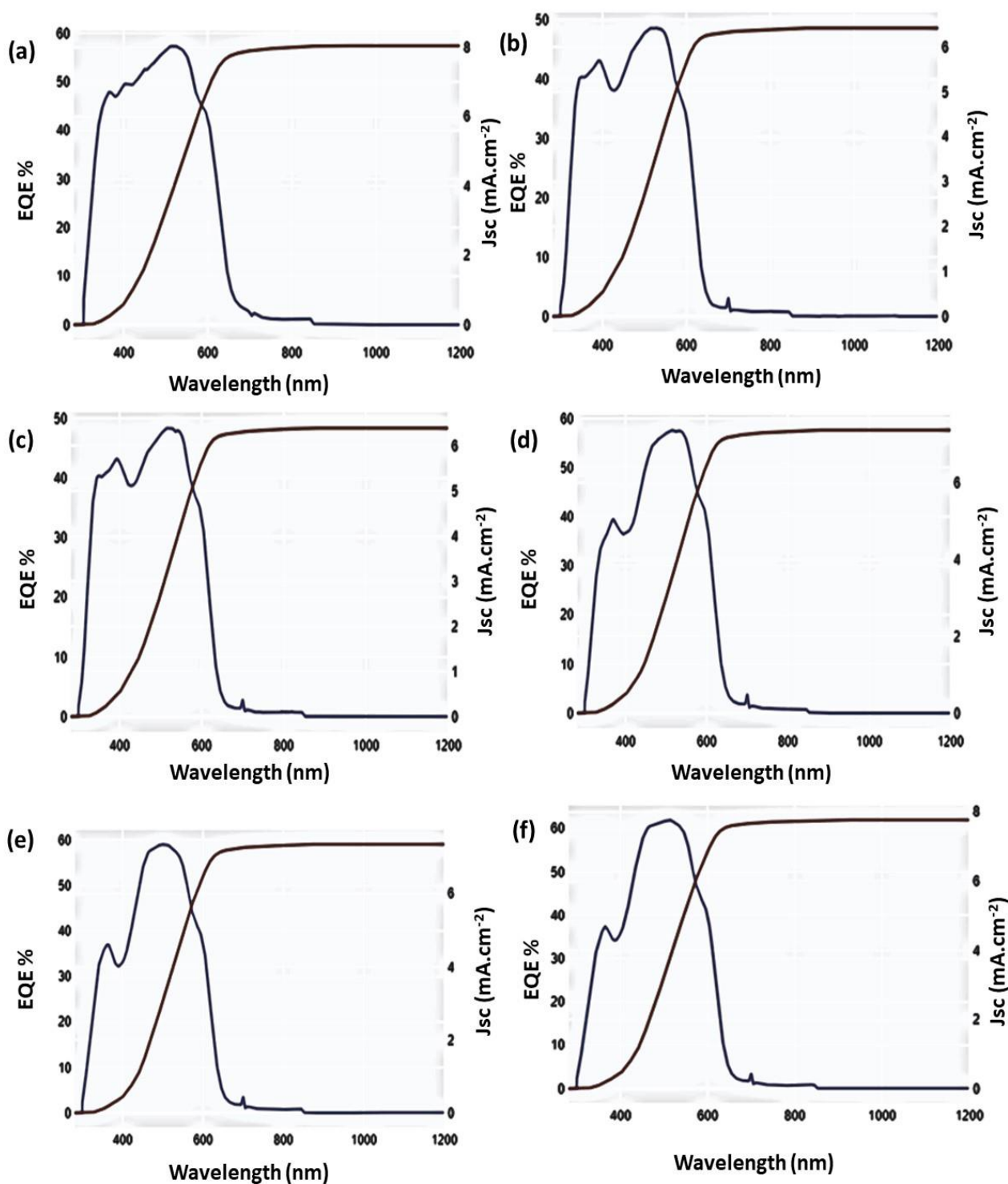


Figure S5. The J_{sc} and EQE relations under different wavelengths for (a) 900, (b) 1000, (c) 1200, (d) 1500, (e) 2000, and (f) 3000 rpm for the active layer using Mg-Al cathode.

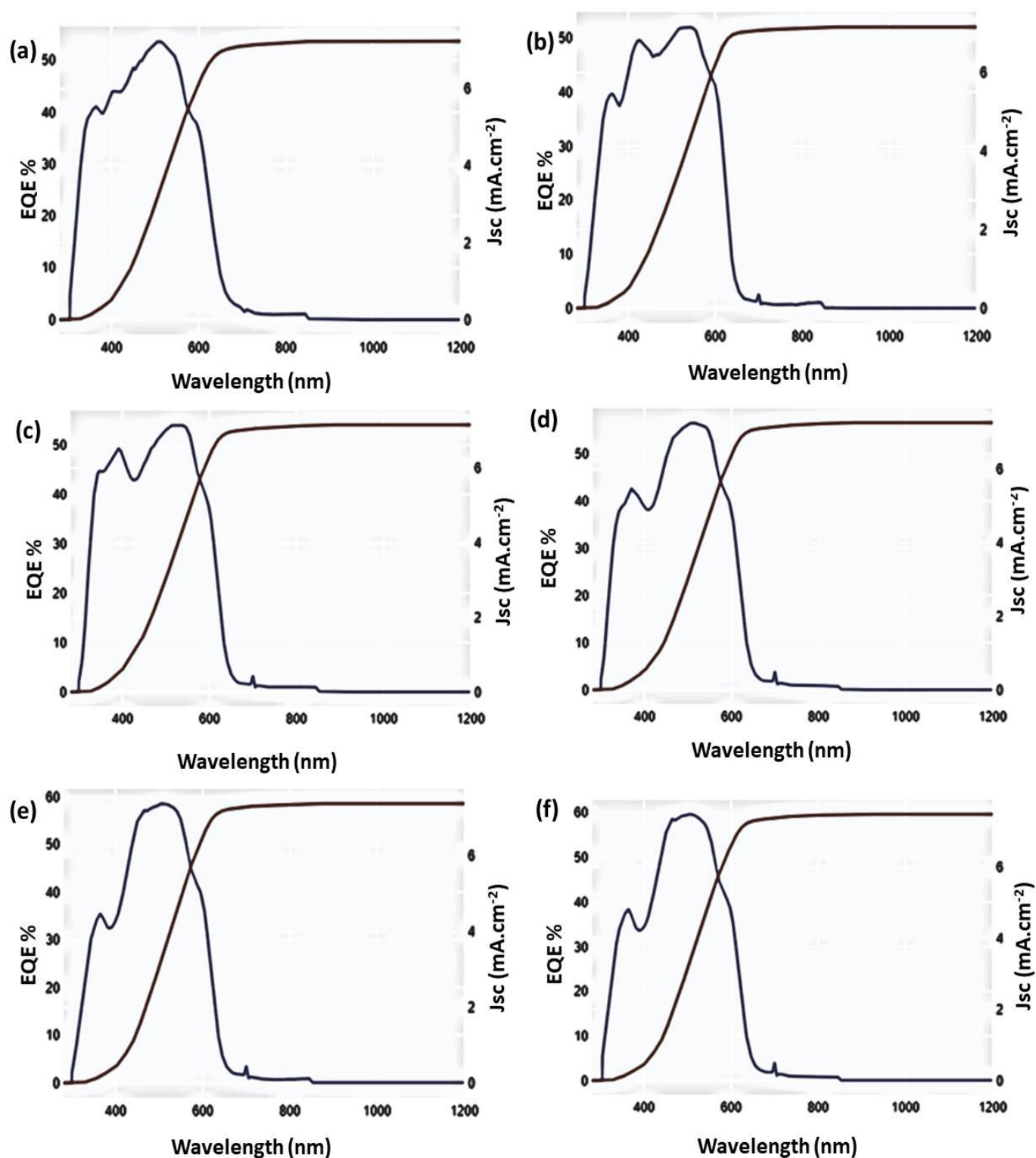


Figure S6. The J_{sc} and EQE relations under different wavelengths for (a) 900, (b) 1000, (c) 1200, (d) 1500, (e) 2000, and (f) 3000 rpm for the active layer using Al cathode.

Table S1. the J_{sc} values calculated from EQE values from Figure S4 under different annealing temperatures for the active layer.

Annealing Temperature (°C)	J_{sc} (mA/cm ²)
130	7.08
140	7.37
150	7.06
160	7.10
170	6.66
180	5.54
190	5.59

Table S2. the J_{sc} values calculated from EQE values from Figures S5 and S6 under different spin speed coating for the active layer.

Spin Frequency (rpm)	Cathode	J_{sc} (mA/cm ²)
900	Mg-Al	8.04
1000	Mg-Al	6.42
1200	Mg-Al	6.39
1500	Mg-Al	7.37
2000	Mg-Al	7.35
3000	Mg-Al	7.76
900	Al	7.24
1000	Al	7.15
1200	Al	7.14
1500	Al	7.27
2000	Al	7.38
3000	Al	7.47